

## **THERMAL OXIDATION GaAs AT THE JOINTLY AND SPATIALLY PARTED INFLUENCE OF OXIDES OF LEAD (II) AND MANGANESE (IV)**

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The influence of PbO and MnO<sub>2</sub> variable compositions on the process of GaAs thermal oxidation was investigated. The observed nonlinear effect of their mutual influence was caused by chemical interaction between oxides, resulting to various inclusions of activators in the oxide layer growing on the surface of GaAs. It was shown, that the interactions between activators resulting to nonlinear dependence of oxide layer thickness on the surface of GaAs, are located mainly in initial compositions of activators and in a vapor phase.